National Semiconductor

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100344
Low Power 8-Bit Latch with Cut-Off Drivers

General Description

The 100344 contains eight D-type latches, individual inputs (D_n), outputs (Q_n), a common enable pin ($\overline{E}$), latch enable ($\overline{LE}$), and output enable pin ($\overline{OEN}$). A Q output follows its D input when both $\overline{E}$ and $\overline{LE}$ are LOW. When either $\overline{E}$ or $\overline{LE}$ (or both) are HIGH, a latch stores the last valid data present on its D input prior to $\overline{E}$ or $\overline{LE}$ going HIGH.

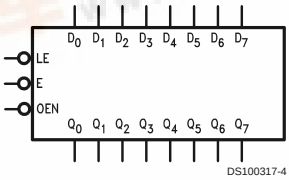
A HIGH on $\overline{OEN}$ holds the outputs in a cut-off state. The cut-off state is designed to be more negative than a normal ECL LOW level. This allows the output emitter-followers to turn off when the termination supply is −2.0V, presenting a high impedance to the data bus. This high impedance reduces termination power and prevents loss of low state noise margin when several loads share the bus.

The 100344 outputs are designed to drive a doubly terminated 50Ω transmission line (25Ω load impedance). All inputs have 50 kΩ pull-down resistors.

Features

- Cut-off drivers
- Drives 25Ω load
- Low power operation
- 2000V ESD protection
- Voltage compensated operating range = −4.2V to −5.7V
- Available to MIL-STD-883

Logic Symbol

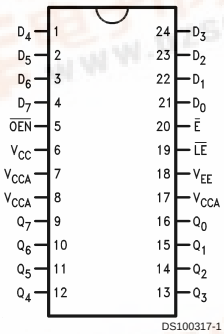


DS100317-4

Pin Names	Description
D_0–D_7	Data Inputs
$\overline{E}$	Enable Input
$\overline{LE}$	Latch Enable Input
$\overline{OEN}$	Output Enable Input
Q_0–Q_7	Data Outputs

Connection Diagrams

24-Pin DIP

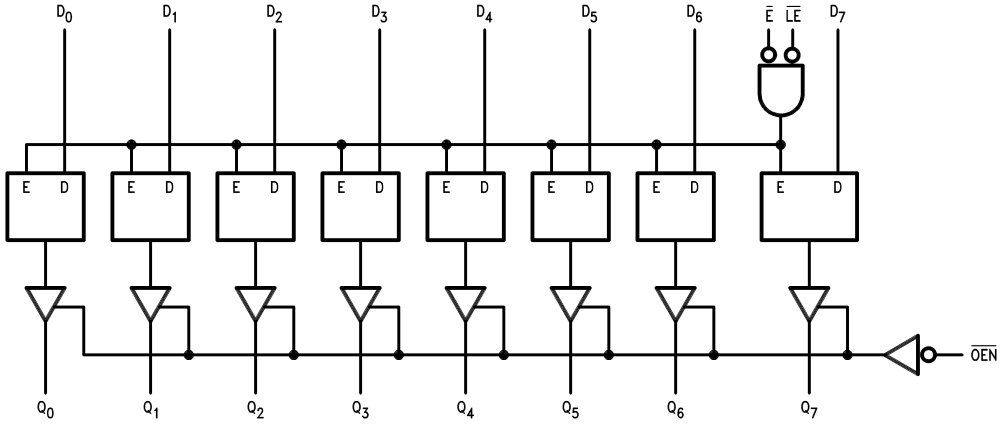


DS100317-1

24-Pin Quad Cerpak

DS100317-2

Logic Diagram



DS100317-5

Truth Table

Inputs				Outputs
D_n	$\overline{E}$	$\overline{LE}$	$\overline{OEN}$	Q_n
L	L	L	L	L
H	L	L	L	H
X	H	X	L	Latched (Note 1)
X	X	H	L	Latched (Note 1)
X	X	X	H	Cutoff

H = HIGH Voltage level
L = LOW Voltage level
Cutoff = lower-than-LOW state

X = Don't Care

Note 1: Retains data present before either $\overline{LE}$ or $\overline{E}$ go HIGH.

Absolute Maximum Ratings (Note 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Above which the useful life may be impaired

Storage Temperature (T_{STG})	−65˚C to +150˚C
Maximum Junction Temperature (T_J)	
Ceramic	+175˚C
V_{EE} Pin Potential to Ground Pin	−7.0V to +0.5V
Input Voltage (DC)	V_{EE} to +0.5V
Output Current (DC Output HIGH)	−100 mA
ESD (Note 3)	≥2000V

Recommended Operating Conditions

Case Temperature (T_C)	
Military	−55˚C to +125˚C
Supply Voltage (V_{EE})	−5.7V to −4.2V

Note 2: Absolute maximum ratings are those values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 3: ESD testing conforms to MIL-STD-883, Method 3015.

Military Version

DC Electrical Characteristics

V_{EE} = −4.2V to −5.7V, V_{CC} = V_{CCA} = GND, T_C = −55˚C to +125˚C

Symbol	Parameter	Min	Max	Units	T_C	Conditions		Notes
V_{OH}	Output HIGH Voltage	−1025	−870	mV	0˚C to +125˚C	V_{IN} = V_{IH} (Max) or V_{IL} (Min)	Loading with 25Ω to −2.0V	(Notes 4, 5, 6)
		−1085	−870	mV	−55˚C			
V_{OL}	Output LOW Voltage	−1830	−1620	mV	0˚C to +125˚C			
		−1830	−1555	mV	−55˚C			
V_{OHC}	Output HIGH Voltage	−1035		mV	0˚C to +125˚C	V_{IN} = V_{IH} (Min) or V_{IL} (Max)	Loading with 25Ω to −2.0V	(Notes 4, 5, 6)
		−1085		mV	−55˚C			
V_{OLC}	Output LOW Voltage		−1610	mV	0˚C to +125˚C			
			−1555	mV	−55˚C			
V_{OLZ}	Cutoff LOW Voltage		−1950	mV	0˚C to +125˚C	V_{IN} = V_{IH} (Min) or V_{IL} (Max)	$\overline{OEN}$ = HIGH	(Notes 4, 5, 6)
			−1850		−55˚C			
V_{IH}	Input HIGH Voltage	−1165	−870	mV	−55˚C to +125˚C	Guaranteed HIGH Signal for All Inputs		(Notes 4, 5, 6, 7)
V_{IL}	Input LOW Voltage	−1830	−1475	mV	−55˚C to +125˚C	Guaranteed LOW Signal for All Inputs		(Notes 4, 5, 6, 7)
I_{IL}	Input LOW Current	0.50		µA	−55˚C to +125˚C	V_{EE} = −4.2V V_{IN} = V_{IL} (Min)		(Notes 4, 5, 6, 7)
I_{IH}	Input HIGH Current		240	µA	0˚C to +125˚C	V_{EE} = −5.7V V_{IN} = V_{IH} (Max)		(Notes 4, 5, 6)
			340	µA	−55˚C			
I_{EE}	Power Supply Current				−55˚C to +125˚C	Inputs Open		(Notes 4, 5, 6)
		−195	−73	mA		V_{EE} = −4.2V to −4.8V		
		−205	−73			V_{EE} = −4.2V to −5.7V		

Note 4: F100K 300 Series cold temperature testing is performed by temperature soaking (to guarantee junction temperature equals −55˚C), then testing immediately without allowing for the junction temperature to stabilize due to heat dissipation after power-up. This provides "cold start" specs which can be considered a worst case condition at cold temperatures.

Note 5: Screen tested 100% on each device at −55˚C, +25˚C, and +125˚C, Subgroups 1, 2, 3, 7, and 8.

Note 6: Sample tested (Method 5005, Table I) on each manufactured lot at −55˚C, +25˚C, and +125˚C, Subgroups A1, 2, 3, 7, and 8.

Note 7: Guaranteed by applying specified input condition and testing V_{OH}/V_{OL}.

AC Electrical Characteristics

V_{EE} = −4.2V to −5.7V, V_{CC} = V_{CCA} = GND

Symbol	Parameter	T_C = −55°C		T_C = +25°C		T_C = +125°C		Units	Conditions	Notes
		Min	Max	Min	Max	Min	Max			
t_{PLH} t_{PHL}	Propagation Delay D_n to Output	0.50	2.60	0.70	2.60	0.70	3.10	ns	*Figures 1, 2*	(Notes 8, 9, 10, 12)
t_{PLH} t_{PHL}	Propagation Delay $\overline{LE}$, $\overline{E}$ to Output	0.80	3.30	1.00	3.30	1.10	3.80	ns	*Figures 1, 4*	(Notes 8, 9, 10, 12)
t_{PZH} t_{PHZ}	Propagation Delay $\overline{OEN}$ to Output	1.00 0.70	4.60 3.00	1.10 0.70	4.20 2.80	1.20 0.70	4.40 3.20	ns	*Figures 1, 2*	(Notes 8, 9, 10, 12)
t_{TLH} t_{THL}	Transition Time 20% to 80%, 80% to 20%	0.40	2.50	0.40	2.40	0.40	2.70	ns	*Figures 1, 3*	(Note 11)
t_s	Setup Time D_0–D_7	1.50		1.50		1.70		ns	*Figures 1, 3*	(Note 11)
t_h	Hold Time D_0–D_7	0.60		0.60		0.60		ns	*Figures 1, 3*	(Note 11)
t_{pw}(H)	Pulse Width HIGH $\overline{LE}$, $\overline{E}$	2.40		2.40		2.40		ns	*Figures 1, 3*	(Note 11)

Note 8: F100K 300 Series cold temperature testing is performed by temperature soaking (to guarantee junction temperature equals −55°C), then testing immediately after power-up. This provides "cold start" specs which can be considered a worst case condition at cold temperatures.

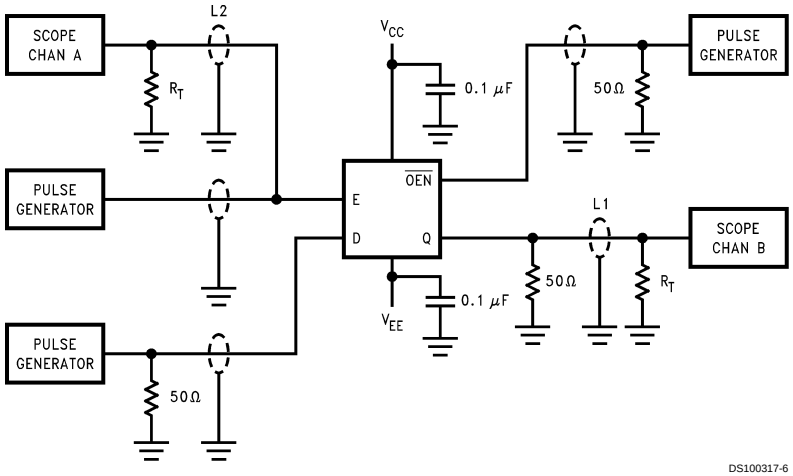
Note 9: Screen tested 100% on each device at +25°C temperature only, Subgroup A9.

Note 10: Sample tested (Method 5005, Table I) on each manufactured lot at +25°C, Subgroup A9, and at +125°C and −55°C temperatures, Subgroups A10 and A11.

Note 11: Not tested at +25°C, +125°C, and −55°C temperature (design characterization data).

Note 12: The propagation delay specified is for single output switching. Delays may vary up to 300 ps with multiple outputs switching.

Test Circuitry



Notes:
V_{CC}, V_{CCA} = +2V, V_{EE} = −2.5V
L1 and L2 = equal length 50Ω impedance lines
R_T = 50Ω terminator internal to scope
Decoupling 0.1 μF from GND to V_{CC} and V_{EE}
All unused outputs are loaded with 25Ω to GND
C_L = Fixture and stray capacitance ≤ 3 pF

FIGURE 1. AC Test Circuit

Switching Waveforms

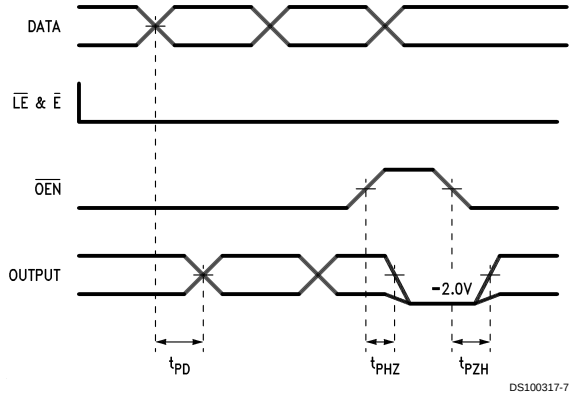


FIGURE 2. Propagation Delay and Cutoff Times

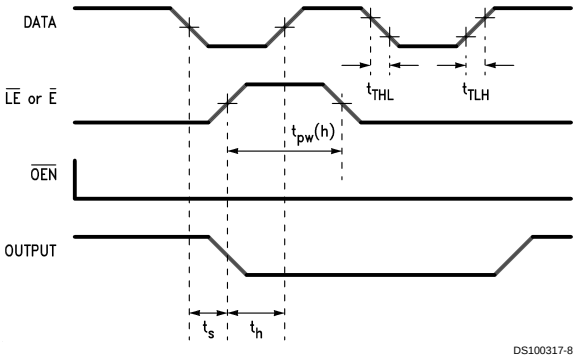


FIGURE 3. Setup, Hold and Pulse Width Times

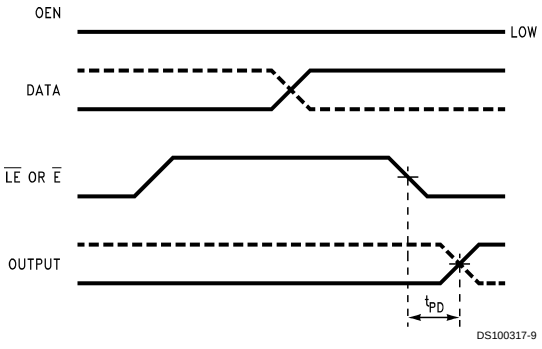
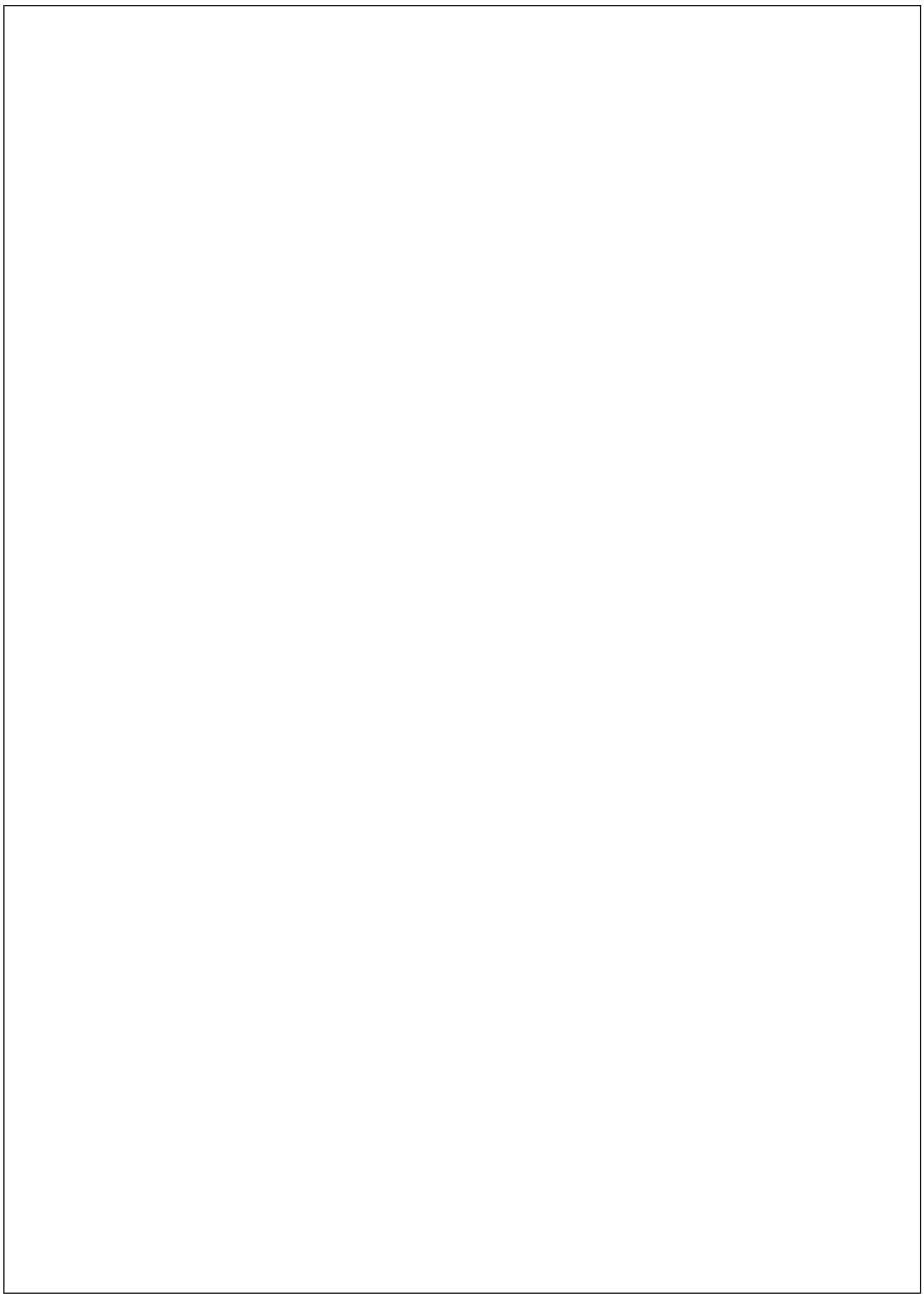
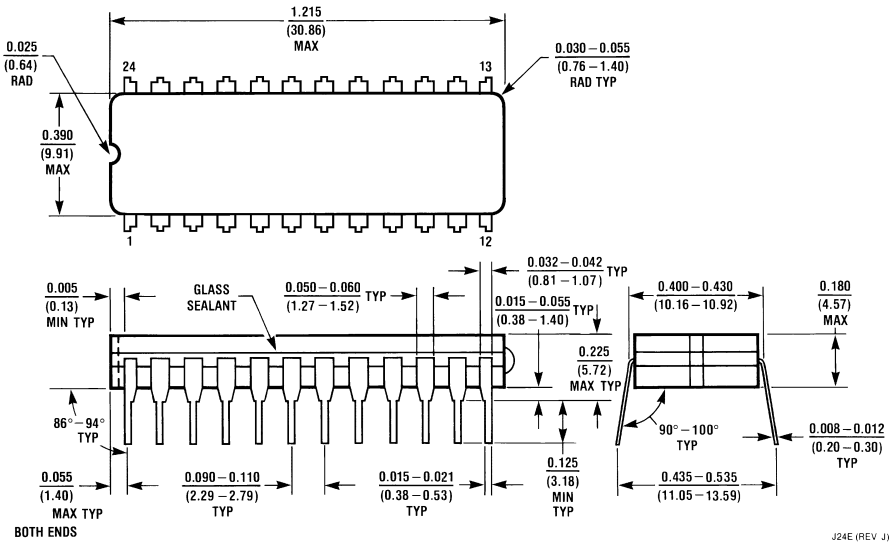


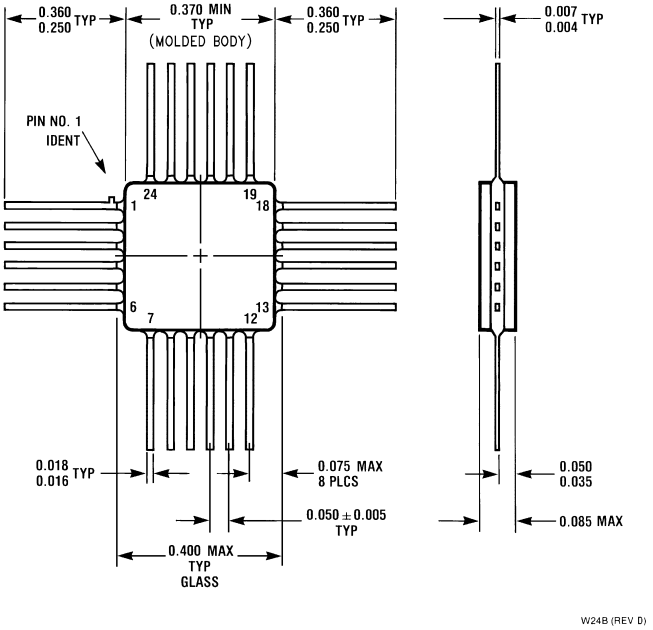
FIGURE 4. Propagation Delay LE, E to Q



Physical Dimensions inches (millimeters) unless otherwise noted



24-Lead Ceramic Dual-In-Line Package (0.400" Wide) (D)
NS Package Number J24E



24-Lead Quad Cerpak (F)
NS Package Number W24B

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